L Number	Hits	Search Text	DB	Time stamp
387	871	(438/238).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/09 09:42
388	269	((438/238).CCLS.) and (SRAM or(static near random near access near memory))	USPAT; US-PGPUB	2003/12/09 09:12
389	269	((438/238).CCLS.) and (SRAM or(static near random near access near memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/09 09:13
390	3	("5330930" | "5365104" | "5877059").PN.	USPAT	2003/12/09 09:28
391	774	(257/903).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/09 09:45
–	31345	SRAM (static near random near access near memory)	USPAT; US-PGPUB	2003/12/09 09:12
–	26244	(SRAM (static near random near access near memory)) and (trench via contact open$)	USPAT; US-PGPUB	2003/12/08 14:13
–	26208	(SRAM (static near random near access near memory)) and (trench via contact open$3)	USPAT; US-PGPUB	2003/12/08 14:14
–	5928	((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3	USPAT; US-PGPUB	2003/12/08 14:15
–	4948	(((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)	USPAT; US-PGPUB	2003/12/08 14:15
–	4059	((((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)) and resist$6	USPAT; US-PGPUB	2003/12/08 14:16
–	3615	(((((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)) and resist$6) and gate	USPAT; US-PGPUB	2003/12/08 14:16
–	3349	((((((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)) and resist$6) and gate) and transistor	USPAT; US-PGPUB	2003/12/08 14:17
–	76	(((((((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)) and resist$6) and gate) and transistor) and (horizontal near10 transistor)	USPAT; US-PGPUB	2003/12/08 14:17
–	280	(((((((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)) and resist$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	USPAT; US-PGPUB	2003/12/08 17:43
–	42124	SRAM (static near random near access near memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/08 17:43
–	283	(((((((SRAM (static near random near access near memory)) and (trench via contact open$3)) and etch$3) and (source drain)) and resist$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/08 18:29
–	870	(438/238).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/09 09:11